

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

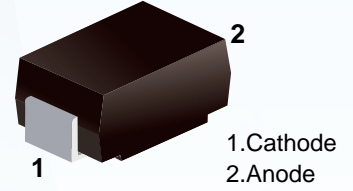
▶ Domestic	Part Number	SS32B - SS320B
▶ Overseas	Part Number	SS32B - SS320B
▶ Equivalent	Part Number	SS32B - SS320B

EV is the abbreviation of name EVVO

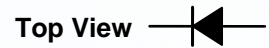
## Schottky Diodes

### Features

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications



**Simplified outline(SMB)**



### Absolute Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbols	SS32B	SS34B	SS36B	SS38B	SS310B	SS312B	SS315B	SS320B	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	40	60	80	100	120	150	200	V
Maximum RMS voltage	$V_{RMS}$	14	28	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	$V_{DC}$	20	40	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	3.0								A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	$I_{FSM}$	80								A
Max Instantaneous Forward Voltage at 3A	$V_F$	0.55	0.70		0.85		0.95		V	
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Reverse Voltage $T_a = 100^\circ\text{C}$	$I_R$	0.5 5			0.3 3				mA	
Typical Junction Capacitance <sup>(1)</sup>	$C_j$	450			400				pF	
Typical Thermal Resistance <sup>(2)</sup>	$R_{\theta JA}$	60								°C/W
Operating Junction Temperature Range	$T_j$	-55 ~ +150								°C
Storage Temperature Range	$T_{stg}$	-55 ~ +150								°C

\* 1 Measured at 1MHz and applied reverse voltage of 4V D.C

\* 2 P.C.B. mounted with 2" × 2" (5×5 cm) copper pad areas.

■ Typical Characteristics

Fig.1 Forward Current Derating Curve

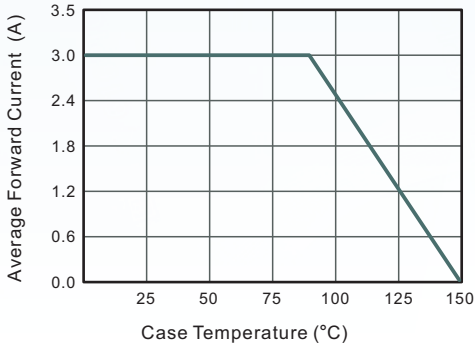


Fig.2 Typical Reverse Characteristics

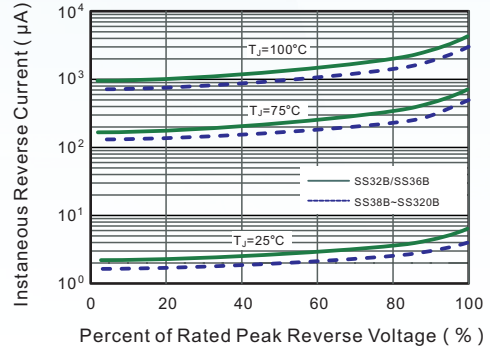


Fig.3 Typical Forward Characteristic

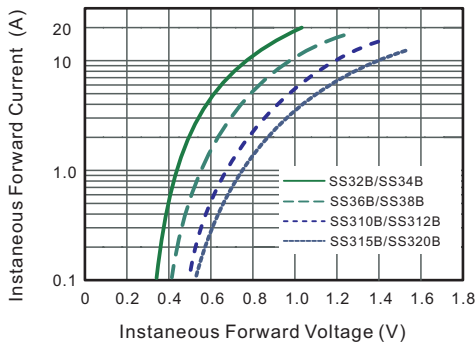


Fig.4 Typical Junction Capacitance

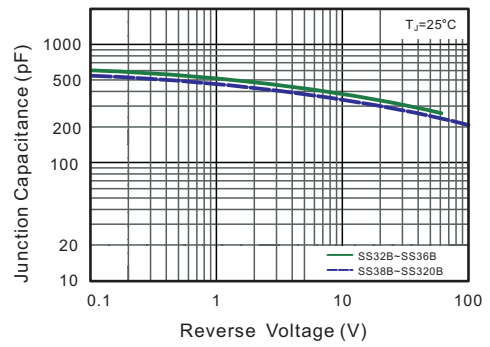


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

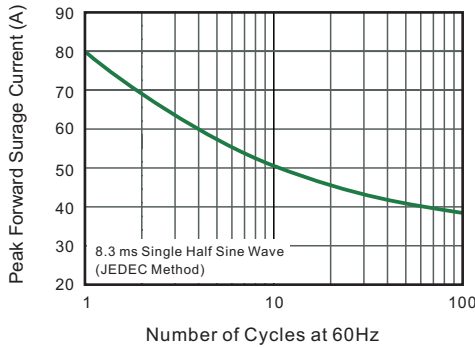
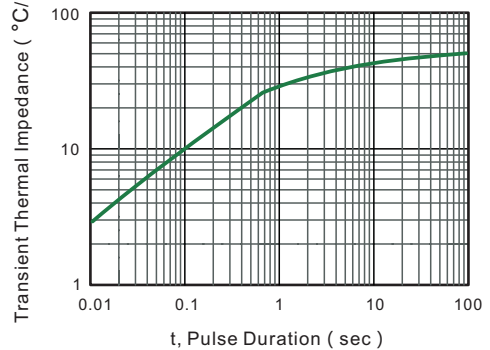
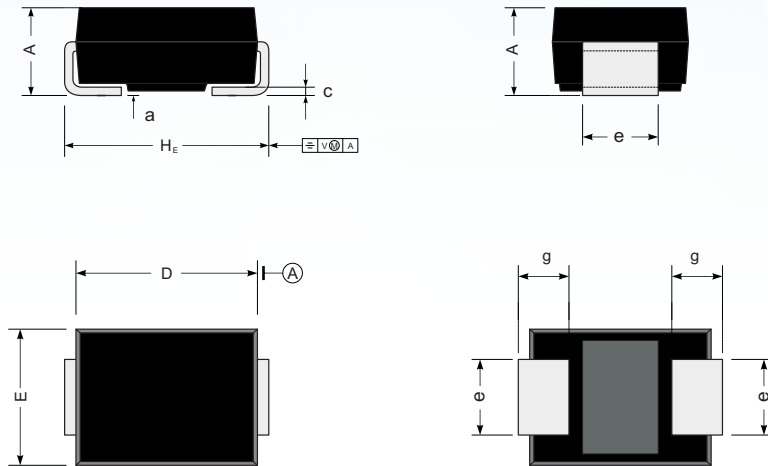


Fig.6 Typical Transient Thermal Impedance

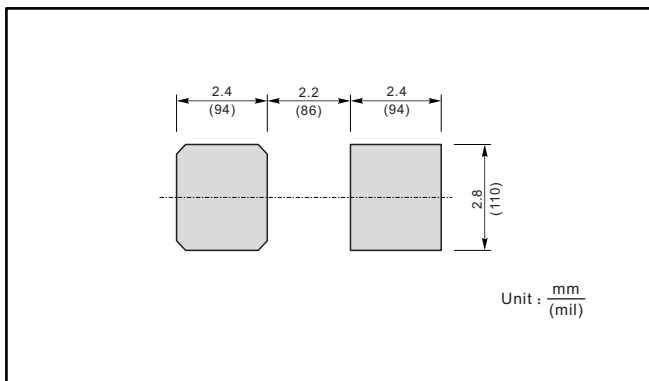


■ SMB



UNIT		A	D	E	H <sub>E</sub>	a	c	e	g
mm	max	2.44	4.83	3.94	5.59	0.21	0.305	2.2	1.5
	min	2.13	4.32	3.3	5.08	0.05	0.152	1.8	0.9
mil	max	96	190	155	220	8.3	12	87	59
	min	83	170	130	200	2.0	6	71	35

The recommended mounting pad size



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